

N-channel TrenchMOS logic level FET Rev. 04 — 31 January 2011

Product data sheet

Suitable for logic level gate drive

Suitable for thermally demanding environments due to 175 °C rating

Motors, lamps and solenoids

sources

Product profile 1.

1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

1.4 Quick reference data

Table 1. Quick reference data Symbol Conditions Parameter Min Max Unit Тур T_i ≥ 25 °C; T_i ≤ 175 °C VDS drain-source voltage -55 V -<u>[1]</u> _ I_{D} drain current V_{GS} = 5 V; T_{mb} = 25 °C; 75 А see Figure 1; see Figure 3 P_{tot} total power dissipation T_{mb} = 25 °C; see Figure 2 253 W -_ Static characteristics R_{DSon} drain-source on-state $V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ -6.4 7.5 mΩ resistance T_i = 25 °C V_{GS} = 4.5 V; I_D = 25 A; 8.5 mΩ --T_j = 25 °C $V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ 6.8 8 mΩ T_j = 25 °C; see Figure 11; see Figure 12

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Table 1.	Quick reference data	continued				
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} &I_D = 75 \text{ A}; \text{V}_{\text{sup}} \leq 55 \text{ V}; \\ &R_{\text{GS}} = 50 \Omega; \text{V}_{\text{GS}} = 5 \text{ V}; \\ &T_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} \end{split} $	-	-	670	mJ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 44 V; T _j = 25 °C; see <u>Figure 13</u>	-	43	-	nC

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		2
2	D	drain ^[1]	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] Continuous current is limited by package.

[1] It is not possible to make a connection to pin 2.

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9608-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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4. Limiting values

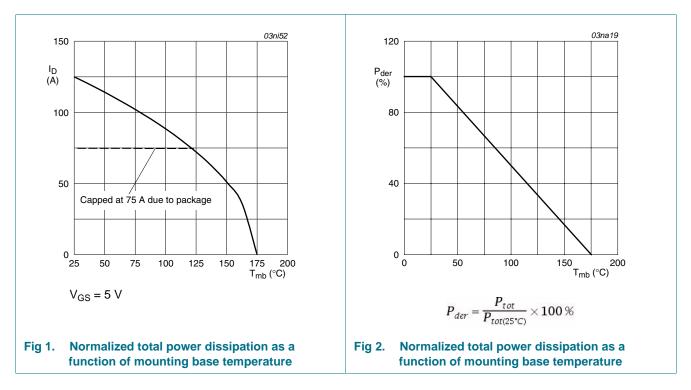
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	55	V
V _{GS}	gate-source voltage			-15	15	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; see <u>Figure 1;</u>	[1]	-	125	А
		see <u>Figure 3</u>	[2]	-	75	А
		T_{mb} = 100 °C; V_{GS} = 5 V; see <u>Figure 1</u>	[2]	-	75	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; see Figure 3		-	503	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	253	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C	[1]	-	125	А
			[2]	-	75	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	503	А
Avalanche ru	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 75 A; V _{sup} ≤ 55 V; R _{GS} = 50 Ω; V _{GS} = 5 V; T _{i(init)} = 25 °C; unclamped		-	670	mJ

[1] Current is limited by power dissipation chip rating.

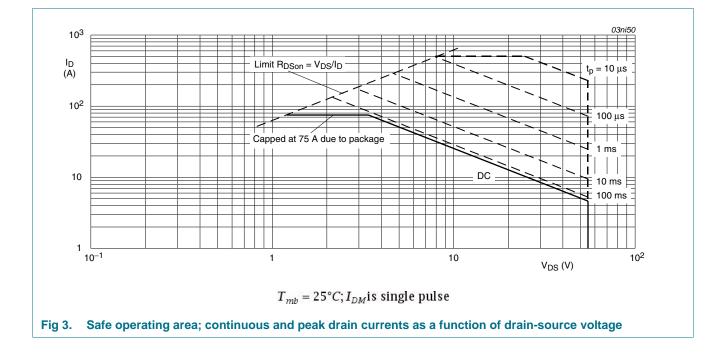
[2] Continuous current is limited by package.



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BUK9608-55A

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Thermal characteristics 5.

Table 5.	mermai characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.59	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed-circuit board ; minimum footprint	-	50	-	K/W

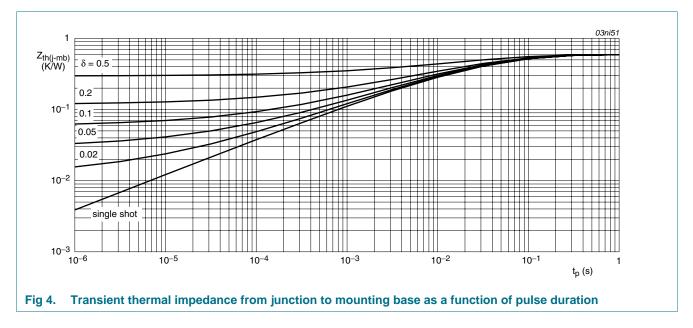


Table 5 Thermal characteristics

6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara		Conditions		ЧŲ	max	onic
V _{(BR)DSS}	drain-source breakdown	I _D = 0.25 mA; V _{GS} = 0 V; T _i = 25 °C	55		-	V
(BR)DSS	voltage	$I_D = 0.25 \text{ m/s}, V_{GS} = 0 \text{ V}; T_i = -55 \text{ °C}$	50	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 0.25$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C;	1	1.5	2	V
		see Figure 10				
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 10</u>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	2.3	V
I _{DSS}	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
Deen	drain-source on-state	V_{GS} = 10 V; I _D = 25 A; T _j = 25 °C	-	6.4	7.5	mΩ
	resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	16	mΩ
		V_{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C	-	-	8.5	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	6.8	8	mΩ
Dynamic cl	naracteristics					
Q _{G(tot)}	total gate charge	al gate charge $I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 5 \text{ V};$	-	92	-	nC
Q _{GS}	gate-source charge	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{13}$	-	11	-	nC
Q _{GD}	gate-drain charge		-	43	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	4551	6021	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 14$	-	760	900	pF
C _{rss}	reverse transfer capacitance		-	500	687	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $\text{R}_{G(ext)} = 10 \Omega; \text{ T}_{I} = 25 \text{ °C}$	-	40	-	ns
t _r	rise time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $\text{R}_{G(ext)} = 10 \Omega; \text{ T}_{I} 25 \text{ °C}$	-	175	-	ns
t _{d(off)}	turn-off delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$	-	280	-	ns
t _f	fall time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	167	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25 \text{ °C}$	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ °C}$	-	2.5	2.5 -	nH
L _S	internal source inductance	from source lead to source bond pad ; T _i = 25 °C	-	7.5	-	nH

Symbol

BUK9608-55A

Max

Unit

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Тур

Min

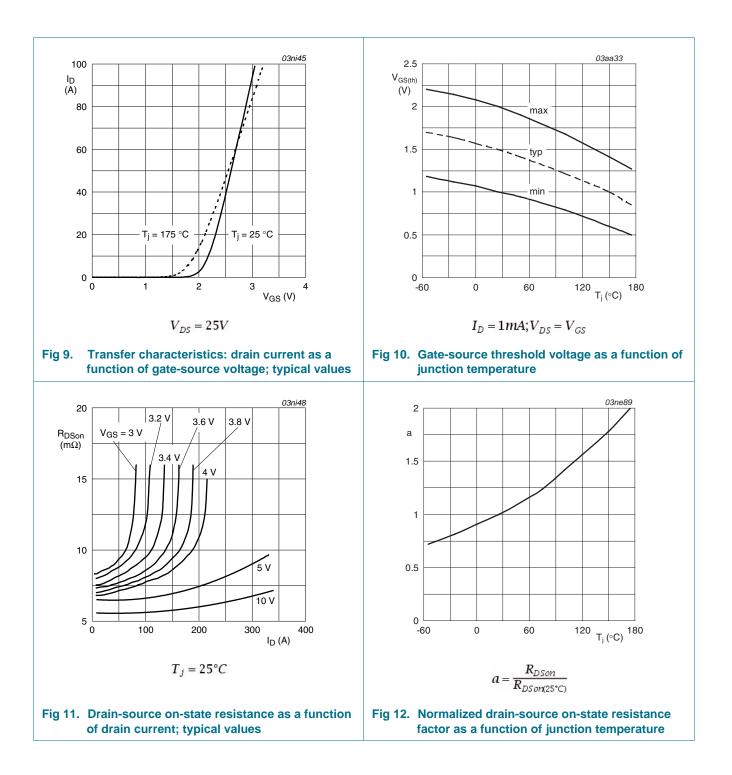
		Conditiono		.76	шал	•
	rain diode					
SD	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 15</u>	-	0.85	1.2	V
r	reverse recovery time	$I_{S} = 75 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	70	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 25 V; T _j = 25 °C	-	170	-	nC
400 I _D (A)	10 8 5 label is V _{GS}	03ni47 9 (V) R _{DSon} (mΩ)			03ni46	
300 200						
100	3.6 3.4 3.2 3 2.8 2.6	6 6				
0		10 5 (V) 5 (V)	5	10 V _G	15 S (V)	
	$T_j = 25^{\circ}C; t_p = 300 \mu s$ Output characteristics: drain curre function of drain-source voltage; t	ent as a Fig 6. Drain-source		esistanc		unctio
10 ⁻¹ I _D (A) 10 ⁻²		120 9fs (S) 100			03ni44	
10 ⁻³	$ \begin{array}{c c} & & & \\ & & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & $	60				
10 ⁻⁵		20				
10 ⁻⁶	0 1 2 V _{GS} (V	0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0	40	60	80 I _D (A)	
		Τ	$25^{\circ}C; V_{DS}$	= 25V		
	$T_j = 25 ^{\circ}C; V_{DS} = V_{GS}$	1 j -	1 5 C, 1 DS	25,		

Conditions

Parameter

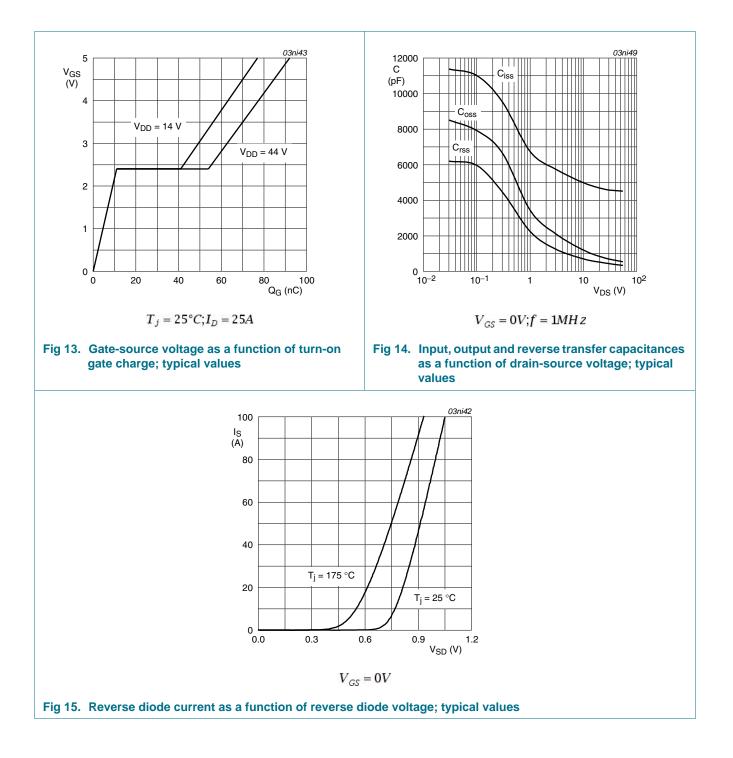
BUK9608-55A

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7. Package outline

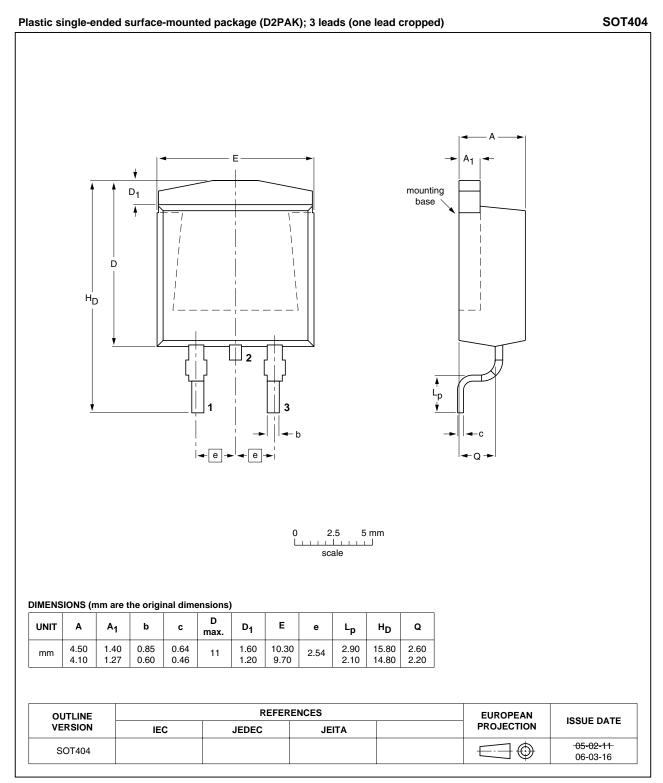


Fig 16. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9608-55A v.4	20110131	Product data sheet	-	BUK95_9608_55A v.3
Modifications:		of this data sheet has be niconductors.	een redesigned to com	ply with the new identity guidelines
	 Legal texts 	have been adapted to t	he new company nam	e where appropriate.
	 Type numb 	er BUK9608-55A separa	ated from data sheet B	UK95_9608_55A v.3.
BUK95_9608_55A v.3	20020506	Product data	-	BUK9508_9608-55A v.2

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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